

Absolute maximum ratings

(Ta=25°C)

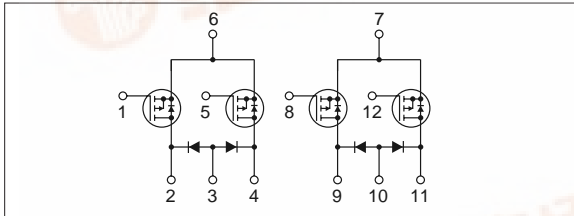
Symbol	Ratings	Unit
V _{DSS}	-100	V
V _{GSS}	±20	V
I _D	±5	A
I _D (pulse)	±10(PW≤1ms)	A
I _F	5(PW≤0.5ms, Du≤25%)	A
I _{FSM}	10(PW≤10ms, Single pulse)	A
V _R	120	V
P _T	5 (Ta=25°C, with all circuits operating, without heatsink) 35 (Tc=25°C, with all circuits operating, with infinite heatsink)	W
θ _{J-a}	25 (Junction-Air, Ta=25°C, with all circuits operating)	°C/W
θ _{J-c}	3.57 (Junction-Case, Tc=25°C, with all circuits operating)	°C/W
V _{ISO}	1000 (Between fin and lead pin, AC)	Vrms
T _{ch}	150	°C
T _{stg}	-40 to +150	°C

Electrical characteristics

(Ta=25°C)

Symbol	Specification			Unit	Condition
	min	typ	max		
V _{(BR)DSS}	-100			V	I _D =-250μA, V _{GS} =0V
I _{GSS}			±500	nA	V _{GS} =±20V
I _{DSS}			-250	μA	V _{DS} =-100V, V _{GS} =0V
V _{TH}	-2.0		-4.0	V	V _{DS} =-10V, I _D =-250μA
R _{e(yfs)}	0.9	2.0		S	V _{DS} =-10V, I _D =-5A
R _{DS(ON)}		0.55	0.7	Ω	V _{GS} =-10V, I _D =-5A
C _{iss}		300		pF	V _{DS} =-25V, f=1.0MHz, V _{GS} =0V
C _{oss}		200		pF	
t _{on}		150		ns	I _D =-5A, V _{DD} =-50V, V _{GS} =-10V,
t _{off}		200		ns	see Fig. 4 on page 16.
V _{SD}	-4.5	-5.5		V	I _{SD} =-5A, V _{GS} =0V
t _{rr}		220		ns	I _{SD} =±100mA

Equivalent circuit diagram

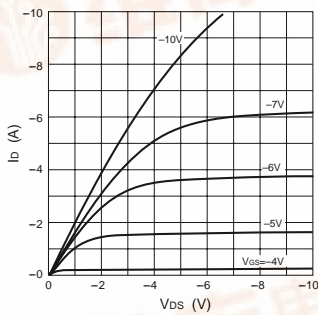


Diode for flyback voltage absorption

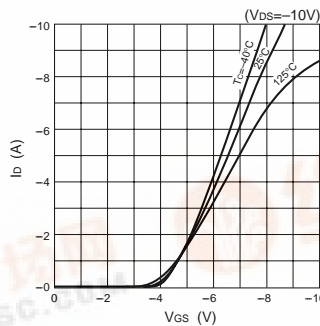
Symbol	Specification			Unit	Condition
	min	typ	max		
V _R	120			V	I _R =10μA
V _F		1.0	1.2	V	I _F =1A
I _R			10	μA	V _R =120V
t _{rr}		100		ns	I _F =±100mA

Characteristic curves

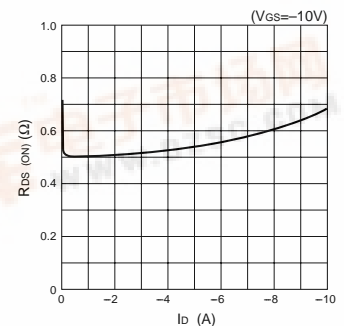
I_D-V_{DS} Characteristics (Typical)



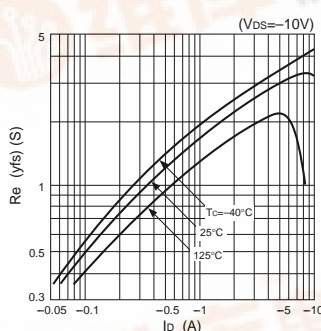
I_D-V_{GS} Characteristics (Typical)



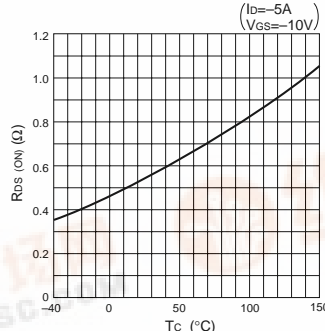
R_{DS(ON)}-I_D Characteristics (Typical)



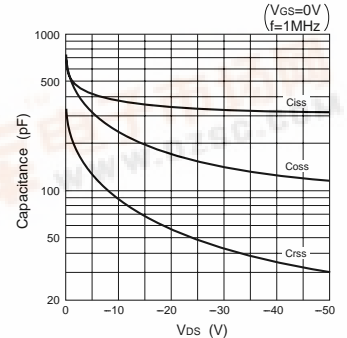
R_{e(yfs)}-I_D Characteristics (Typical)



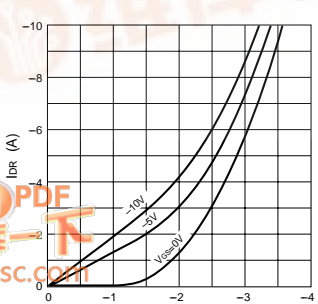
R_{DS(ON)}-T_c Characteristics (Typical)



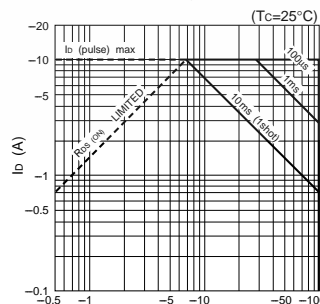
Capacitance-V_{DS} Characteristics (Typical)



I_{DR}-V_{SD} Characteristics (Typical)



Safe Operating Area (SOA)



P_T-T_a Characteristics

